

WHAT IS CLAIMED IS:

1. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

5       applying a reverse bias to the light emitting element;  
determining fault portions of the light emitting element; and  
irradiating a laser to the fault portions.

2. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

10       applying a reverse bias to the light emitting element;  
determining fault portions of the light emitting element by detecting light emitting positions; and  
15       irradiating a laser to the fault portions.

3. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

20       applying a reverse bias to the light emitting element;  
determining fault portions of the light emitting element; and  
irradiating a laser to the fault portions, making the fault portions insulating.

4. A method of manufacturing a light emitting device having a light emitting

element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element by detecting light emitting

5 positions; and

irradiating a laser to the fault portions, making the fault portions insulating.

5. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

determining fault portions of the light emitting element; and

irradiating a laser to the fault portions, making inverse direction electric current flow smaller than before the laser irradiation.

6. A method of manufacturing a light emitting device having a light emitting element composed of an anode, a cathode, and an organic compound layer, comprising the steps of:

applying a reverse bias to the light emitting element;

20 determining fault portions of the light emitting element by detecting light emitting positions; and

irradiating a laser to the fault portions, making inverse direction electric current flow smaller than before the laser irradiation.

7. A method of manufacturing a light emitting device according to claim 1, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

5 8. A method of manufacturing a light emitting device according to claim 2, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

9. A method of manufacturing a light emitting device according to claim 3, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

10. A method of manufacturing a light emitting device according to claim 4, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

11. A method of manufacturing a light emitting device according to claim 5, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

20 12. A method of manufacturing a light emitting device according to claim 6, wherein the organic compound layer contacts the cathode, and the anode contacts the organic compound layer.

13. A method of manufacturing a light emitting device according to claim 1, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

5 14. A method of manufacturing a light emitting device according to claim 2, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

15. A method of manufacturing a light emitting device according to claim 3, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

16. A method of manufacturing a light emitting device according to claim 4, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

17. A method of manufacturing a light emitting device according to claim 5, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

20 18. A method of manufacturing a light emitting device according to claim 6, wherein the organic compound layer comprises light emitting layers, hole injecting layers, hole transporting layers, electron transporting layers, and electron injecting layers.

19. A method of manufacturing a light emitting device according to claim 1,  
further having at least a thin film transistor.

5 20. A method of manufacturing a light emitting device according to claim 2,  
further having at least a thin film transistor.

21. A method of manufacturing a light emitting device according to claim 3,  
further having at least a thin film transistor.

22. A method of manufacturing a light emitting device according to claim 4,  
further having at least a thin film transistor.

23. A method of manufacturing a light emitting device according to claim 5,  
further having at least a thin film transistor.

24. A method of manufacturing a light emitting device according to claim 6,  
further having at least a thin film transistor.

20 25. A method of manufacturing a light emitting device according to claim 1,  
wherein the reverse bias is applied in a range of 1 to 15 V.

26. A method of manufacturing a light emitting device according to claim 2,  
wherein the reverse bias is applied in a range of 1 to 15 V.

27. A method of manufacturing a light emitting device according to claim 3, wherein the reverse bias is applied in a range of 1 to 15 V.

5 28. A method of manufacturing a light emitting device according to claim 4, wherein the reverse bias is applied in a range of 1 to 15 V.

29. A method of manufacturing a light emitting device according to claim 5, wherein the reverse bias is applied in a range of 1 to 15 V.

30. A method of manufacturing a light emitting device according to claim 6, wherein the reverse bias is applied in a range of 1 to 15 V.

31. A thin film forming apparatus comprising:  
a first film formation chamber for forming an organic compound layer of a light emitting element;  
a second film formation chamber for forming an opposing electrode of the light emitting element;  
a first processing chamber for applying a reverse bias to the light emitting element,  
20 detecting light emission locations of the light emitting element;  
a second processing chamber for irradiating a laser to the light emitting element; and  
a third processing chamber for sealing a light emitting device.

32. A thin film forming apparatus according to claim 31, wherein the first film

formation chamber is a film formation chamber for performing film formation by an evaporation method, or a film formation chamber for performing film formation by an application method.

5           33. A thin film forming apparatus according to claim 31, wherein the first processing chamber has: a means for applying a reverse bias within a range of 1 to 15 V to the light emitting element; and a means for detecting the light emission locations.

34. A method of manufacturing a light emitting device using the thin film forming apparatus according to claim 31, comprising the steps of:

detecting the light emission locations in the first processing chamber;  
irradiating the laser to the light emission locations in the second processing chamber;  
and  
sealing the light emitting element in the third processing chamber.

35. A method of manufacturing a light emitting device according to claim 1, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

20           36. A method of manufacturing a light emitting device according to claim 2, wherein the light emitting device is at least one device selected from the group consisting of: a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type display, a video camera and a cellular phone.

37. A method of manufacturing a light emitting device according to claim 3,  
wherein the light emitting device is at least one device selected from the group consisting of:  
a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type  
5 display, a video camera and a cellular phone.

38. A method of manufacturing a light emitting device according to claim 4,  
wherein the light emitting device is at least one device selected from the group consisting of:  
a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type  
display, a video camera and a cellular phone.

39. A method of manufacturing a light emitting device according to claim 5,  
wherein the light emitting device is at least one device selected from the group consisting of:  
a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type  
display, a video camera and a cellular phone.

40. A method of manufacturing a light emitting device according to claim 6,  
wherein the light emitting device is at least one device selected from the group consisting of:  
a digital still camera, a laptop computer, a mobile computer, a DVD player, a goggle type  
20 display, a video camera and a cellular phone.